

T495X107K025ZTE1507280

Obsolete

B450, Tantalum, MnO₂ Tantalum, 100 uF, 10%, 25 VDC, SMD, Molded, Low ESR, Surge Robust, 150 mOhms, 7343, Height Max = 4.4mm



General Information

Series	B450
Dielectric	MnO ₂ Tantalum
Style	SMD Chip
Description	SMD, Molded, Low ESR, Surge Robust
Features	Low ESR, Surge Robust
RoHS	Yes
Termination	Tin
AEC-Q200	No
Notes	Obsolete. Old Part Number [Obsolete] Was B45025E1076K157.

Specifications

Capacitance	100 uF
Capacitance Tolerance	10%
Voltage DC	25 VDC (85C), 16.75 VDC (125C)
Temperature Range	-55/+125°C
Rated Temperature	85°C
Dissipation Factor	10%
Failure Rate	N/A
Resistance	0.15 Ohms (100kHz)
Ripple Current	1050 mAmps (25C), 945 mAmps (85C), 420 mAmps (125C)
Leakage Current	25 uA

Dimensions

Footprint	7343
L	7.3mm +/-0.3mm
W	4.3mm +/-0.3mm
H	4.1mm +/-0.3mm
S	1.3mm +/-0.3mm
F	2.4mm +/-0.1mm
K	1.8mm TYP

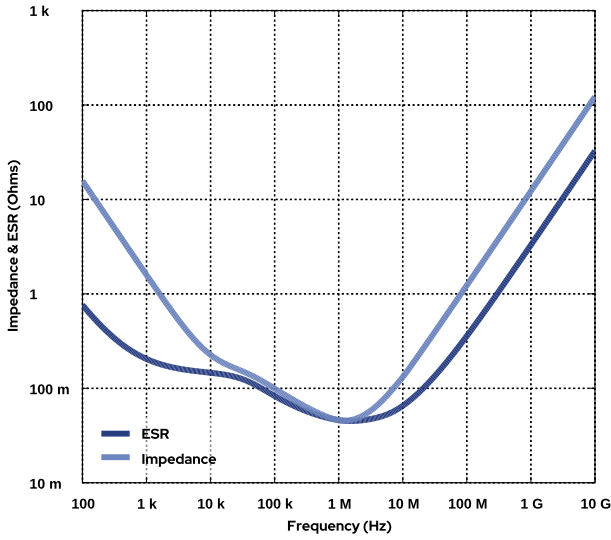
Packaging Specifications

Packaging	T&R, 330mm
Packaging Quantity	1800

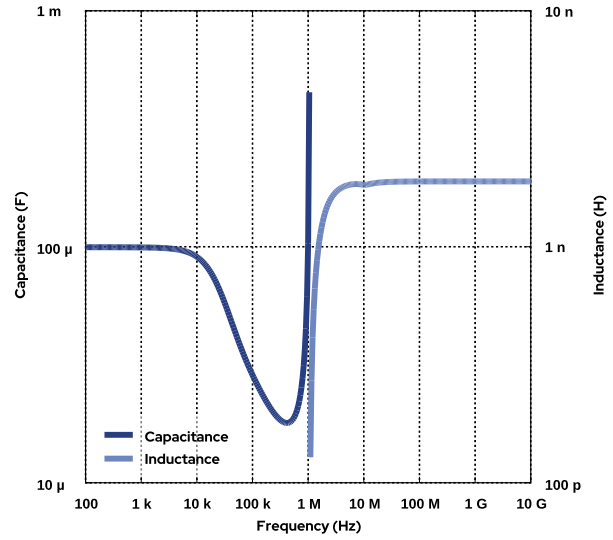
Simulations

For the complete simulation environment please visit [K-SIM](#).

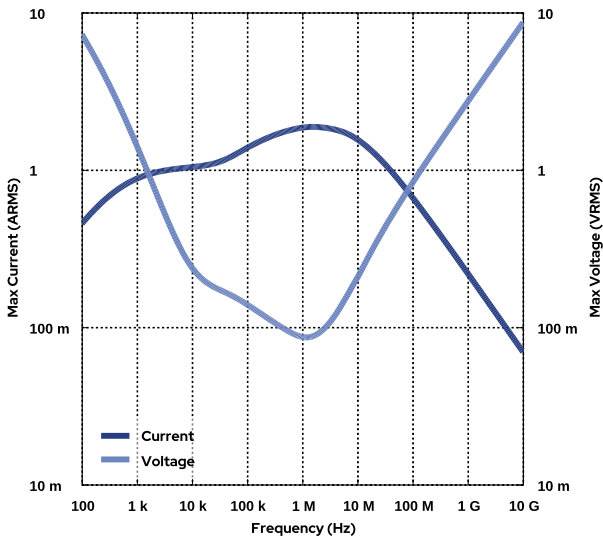
Impedance and ESR



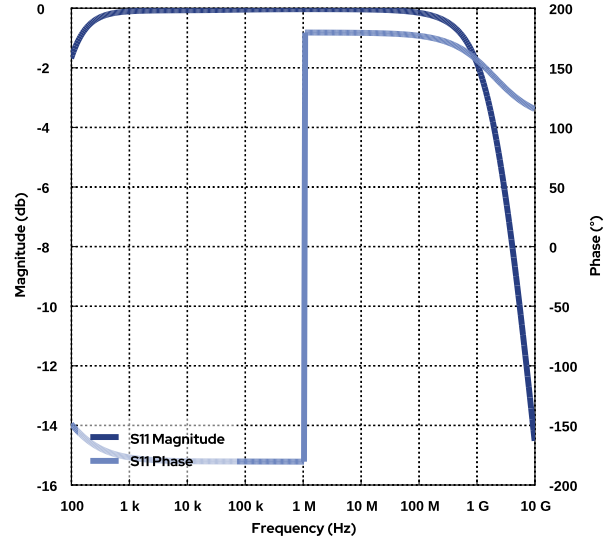
Capacitance and Inductance



Current and Voltage

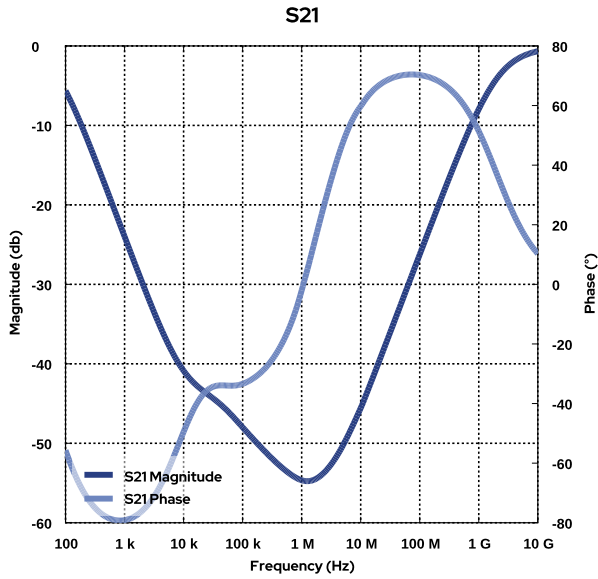


S11



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These are simulations.

This is not a specification!

The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

The responses shown do not represent a specified or implied maximum capability of the device for all applications.

- The ESR used for ripple "Ripple Current/Voltage vs. Frequency" plots is the ESR at ambient temperature.
- The ESR in the "Temperature Rise vs. Ripple Current" plots is adjusted to each incremental temperature rise before the power and ripple current is calculated.
- The effects shown herein are based on measured data from a multiple part sample of the parts in question.
- Ripple capability of this device will be factored by thermal resistance (Rth) created by circuit traces (addi affects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance).
- The peak voltages generated in the "Temperature Rise vs. Combined Ripple Currents" plot are calculated for each frequency and are not combined with voltages generated at any other harmonics.
- Please consult with the catalog or field applications engineer for maximum capability of the device in specific applications.

All product information and data (collectively, the "Information") are subject to change without notice.

KEMET K-SIM is designed to simulate behavior of components with respect to frequency, ambient temperature, and DC bias levels. The responses shown represent the typical response for each part type. Specific responses may vary, depending on manufacturing variation effects of all parameters involved, including the specified tolerances applied to capacitance and unspecified variations of ESR, ESL, and leakage resistance.

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If you have any questions please contact K-SIM.